DISCRETE SEMICONDUCTORS

DATA SHEET

PDTA143E series PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

Product specification Supersedes data of 2003 Sep 08 2004 Aug 04





PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTA143E series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- · Inverter and interface circuits
- · Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
R1	bias resistor	4.7	_	kΩ
R2	bias resistor	4.7	_	kΩ

DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PAC	KAGE	MARKING CODE	NPN COMPLEMENT
I TPE NUMBER	PHILIPS	EIAJ	MARKING CODE	NPN COMPLEMENT
PDTA143EE	SOT416	SC-75	01	PDTC143EE
PDTA143EEF	SOT490	SC-89	50	PDTC143EEF
PDTA143EK	SOT346	SC-59	01	PDTC143EK
PDTA143EM	SOT883	SC-101	DL	PDTC143EM
PDTA143ES	SOT54 (TO-92)	SC-43	TA143E	PDTC143ES
PDTA143ET	SOT23	_	*01 ⁽¹⁾	PDTC143ET
PDTA143EU	SOT323	SC-70	*01 ⁽¹⁾	PDTC143EU

Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTA143E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CYMPOL		PINNING
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION
PDTA143ES	1 R1 R2 R2 R2 R2 R2 R2	1 2 3	base collector emitter
PDTA143EE PDTA143EEF PDTA143EK PDTA143ET PDTA143EU	3 1 R1 R2 2 Top view MDB271	1 2 3	base emitter collector
PDTA143EM	2 R1 3 Bottom view ADB267	1 2 3	base emitter collector

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTA143E series

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	_	-50	V
V _{EBO}	emitter-base voltage	open collector	_	-10	V
V _I	input voltage				
	positive		_	+10	V
	negative		_	-30	V
Io	output current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT23	note 1	_	250	mW
	SOT54	note 1	_	500	mW
	SOT323	note 1	_	200	mW
	SOT346	note 1	_	250	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air		
	SOT23	note 1	500	K/W
	SOT54	note 1	250	K/W
	SOT323	note 1	625	K/W
	SOT346	note 1	500	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTA143E series

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-0.9	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	30	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input-off voltage	$I_C = -100 \mu\text{A}; V_{CE} = -5 \text{V}$	_	-1.1	-0.5	V
V _{i(on)}	input-on voltage	$I_C = -20 \text{ mA}; V_{CE} = -0.3 \text{ V}$	-2.5	-1.9	_	V
R1	input resistor		3.3	4.7	6.1	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	3	pF

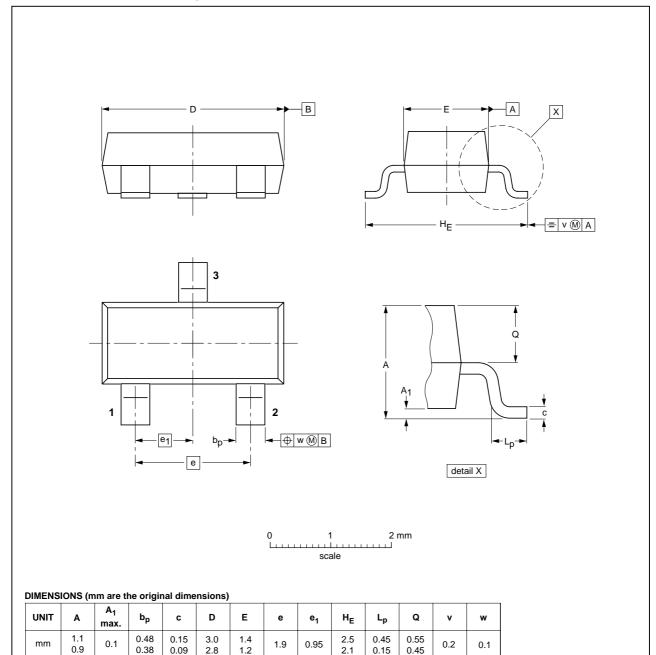
PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTA143E series

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT23



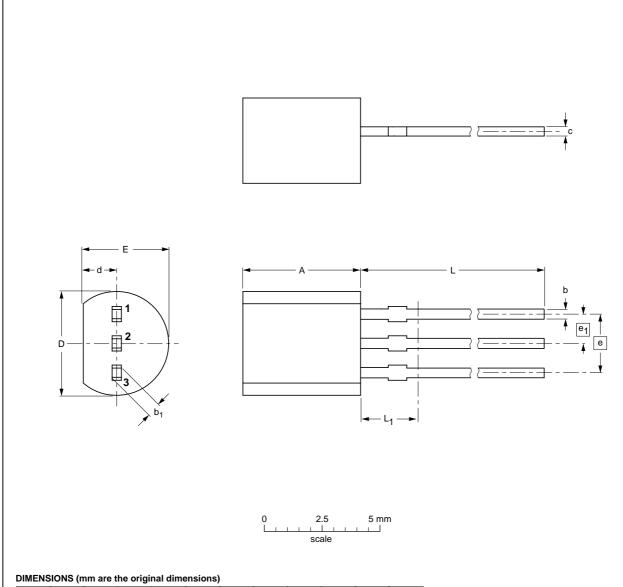
	REFER	EUROPEAN	ISSUE DATE			
IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
	TO-236AB				-97-02-28 99-09-13	
	IEC	IEC JEDEC		IEC JEDEC EIAJ	IEC JEDEC EIAJ PROJECTION	

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTA143E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

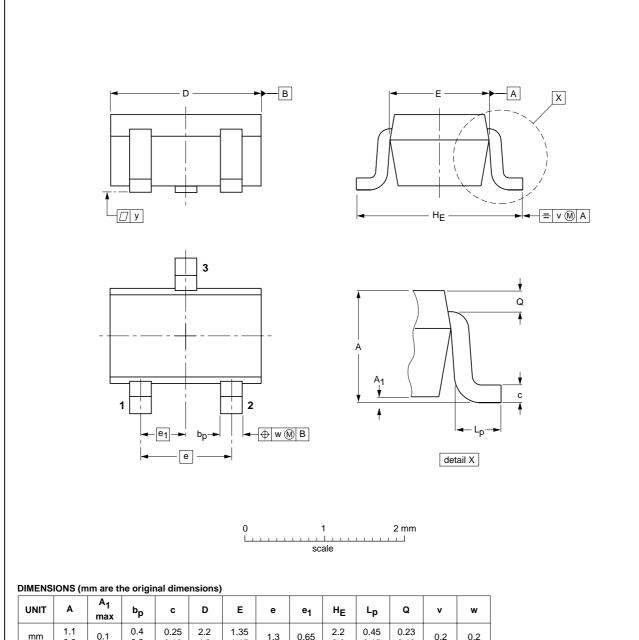
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VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			97-02-28 04-06-28

PNP resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$, $R2 = 4.7 \text{ k}\Omega$

PDTA143E series

Plastic surface mounted package; 3 leads

SOT323



UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT323			SC-70			97-02-28	

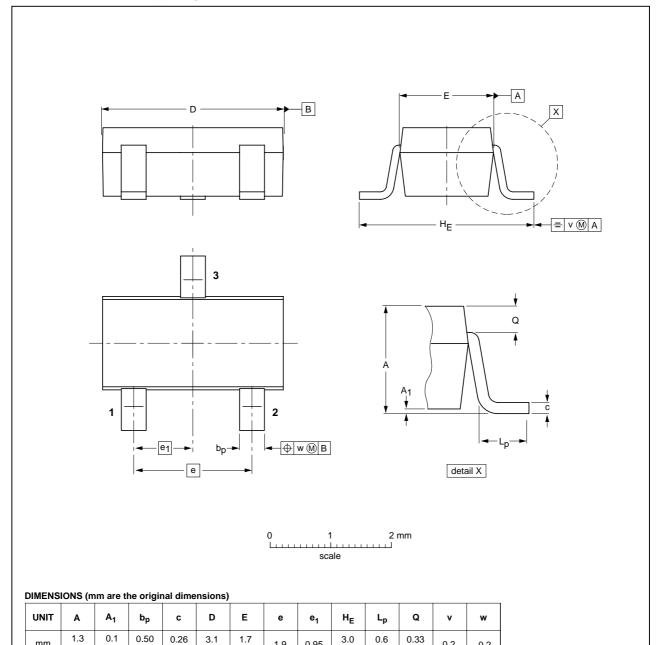
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PNP resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$, $R2 = 4.7 \text{ k}\Omega$

PDTA143E series

Plastic surface mounted package; 3 leads

SOT346



OUTLINE		REFER	EUROPEAN	IOOUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT346		TO-236	SC-59			98-07-17	

0.95

0.2

0.2

1.9

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1.0

0.013

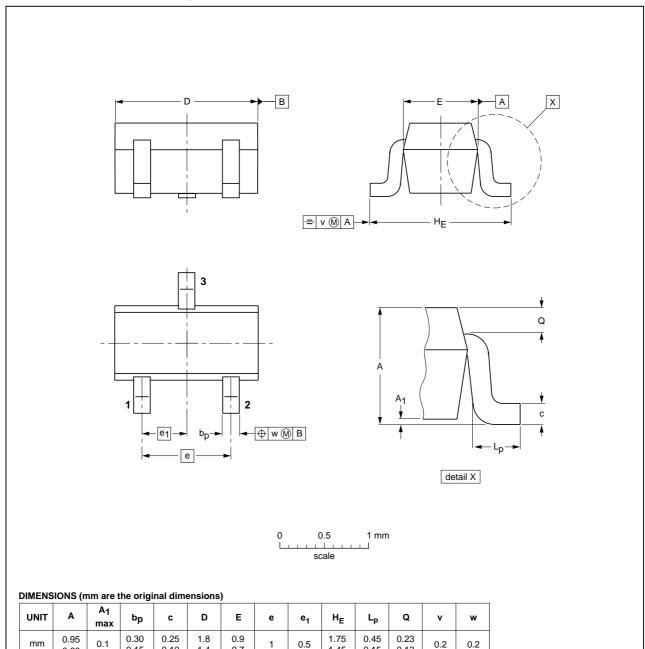
0.35

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTA143E series

Plastic surface mounted package; 3 leads

SOT416



OUTLINE	REFERENCES				EUROPEAN	IOOUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT416			SC-75			97-02-28

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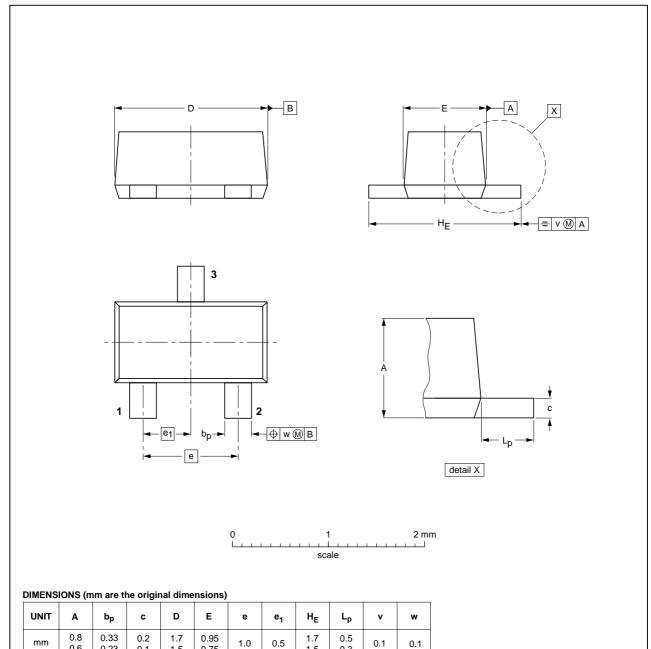
0.10

PNP resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$, $R2 = 4.7 \text{ k}\Omega$

PDTA143E series

Plastic surface mounted package; 3 leads

SOT490



OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT490			SC-89		$\bigoplus \bigoplus$	98-10-23

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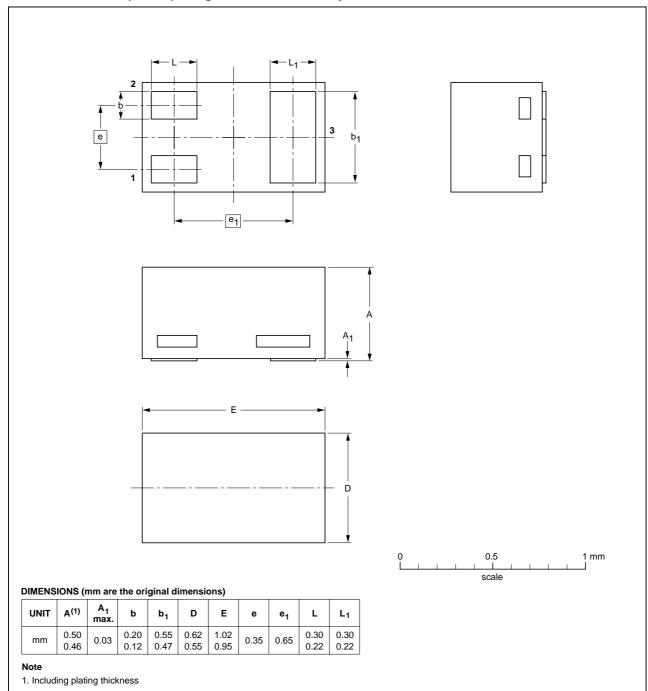
0.6

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTA143E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT883			SC-101			03-02-05 03-04-03

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTA143E series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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